

Recent work on 3D and pixel detectors at IMB-CNM

- Double-sided 3D at CNM
- Recent 3D fabrication runs
 - Strips
 - Medipix2
 - ATLAS pixels
- Bump bonding at IFAE-CNM

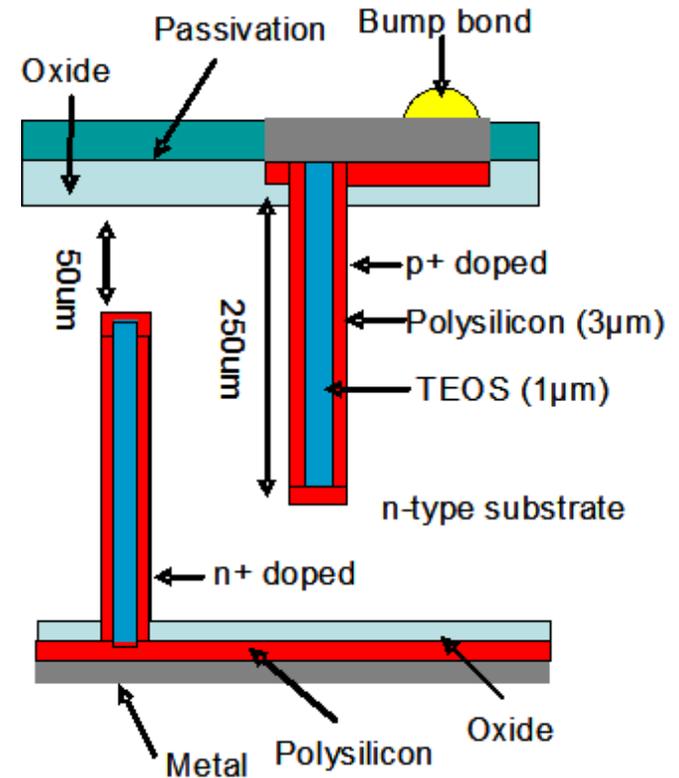
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(CNM, Barcelona)

Reminder: double-sided 3D at CNM

- Columns etched from opposite sides of substrate and don't pass through full thickness
- All fabrication done in-house

Electrode fabrication:

1. ICP etching of the holes: Bosch process, ALCATEL 601-E
2. Holes partially filled with 3 μm LPCVD poly
3. Doping with P or B
4. Holes passivated with 2 μm TEOS SiO_2



Double-sided 3D, n-type

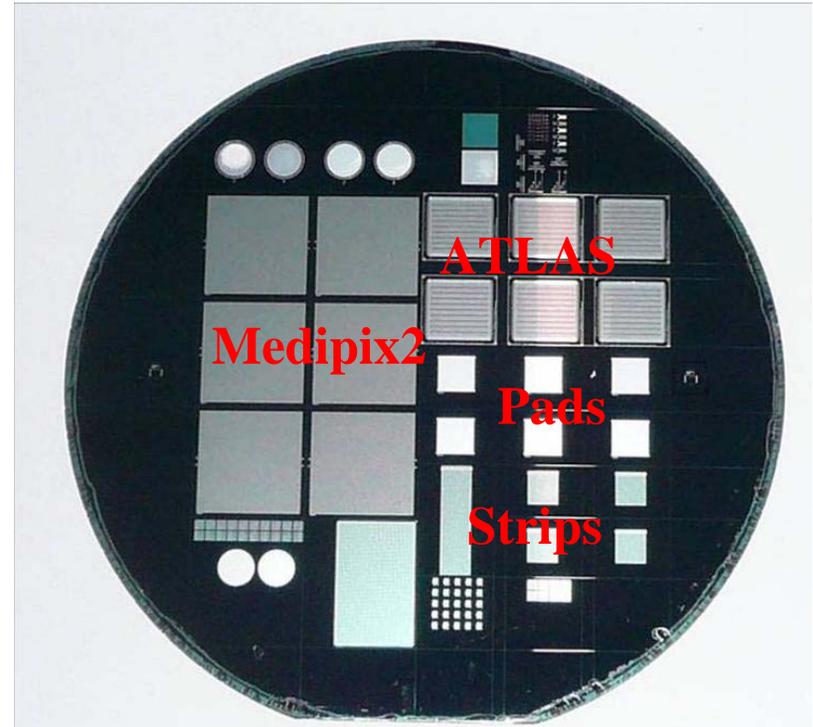
Double-sided 3D fabrication runs

First run (Nov'07): n-type, 2 wafers

- 1 for electrical tests and charge collection with strips,
- 1 for bump bonding of Medipix

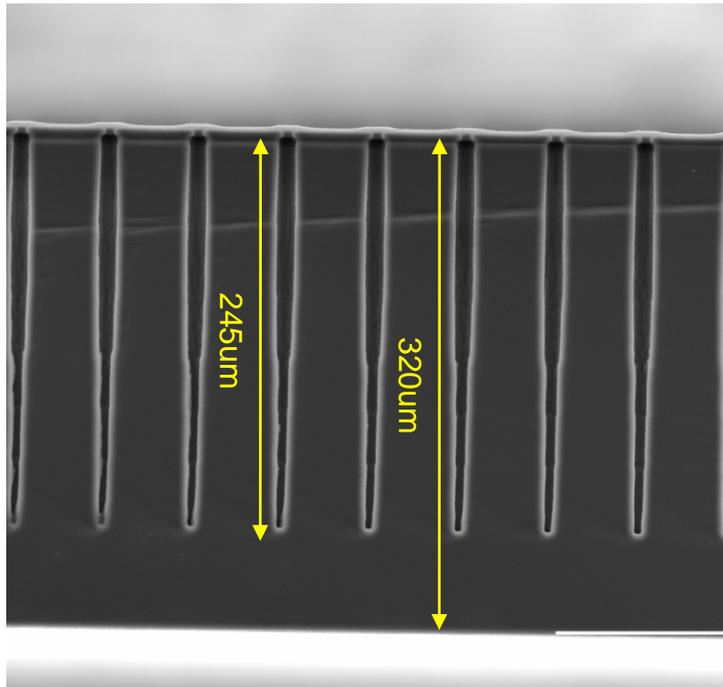
Two new fabrication runs in October 2008:

- 8 n-type wafers - two were damaged during the process
- 8 p-type wafers
 - p-stop isolation
 - Electron collection -> **ATLAS pixels** will be usable

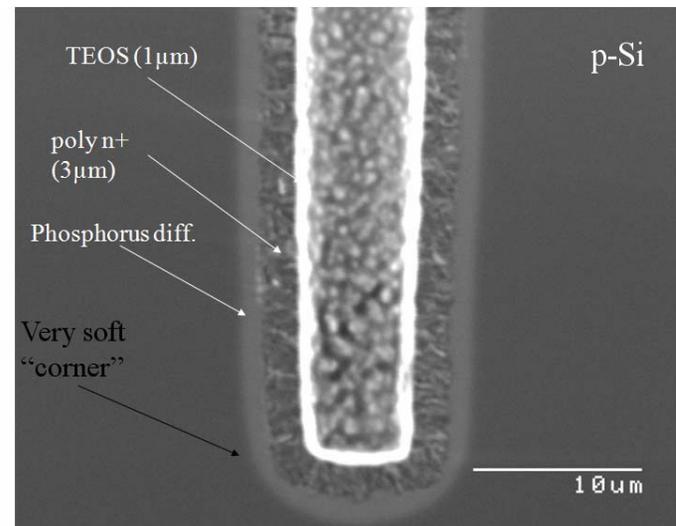
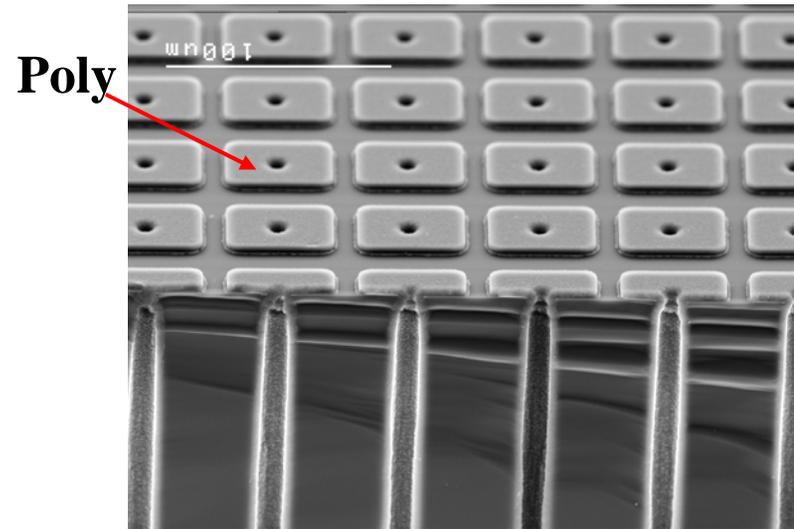


4'' 3D-wafer

3D Electrodes

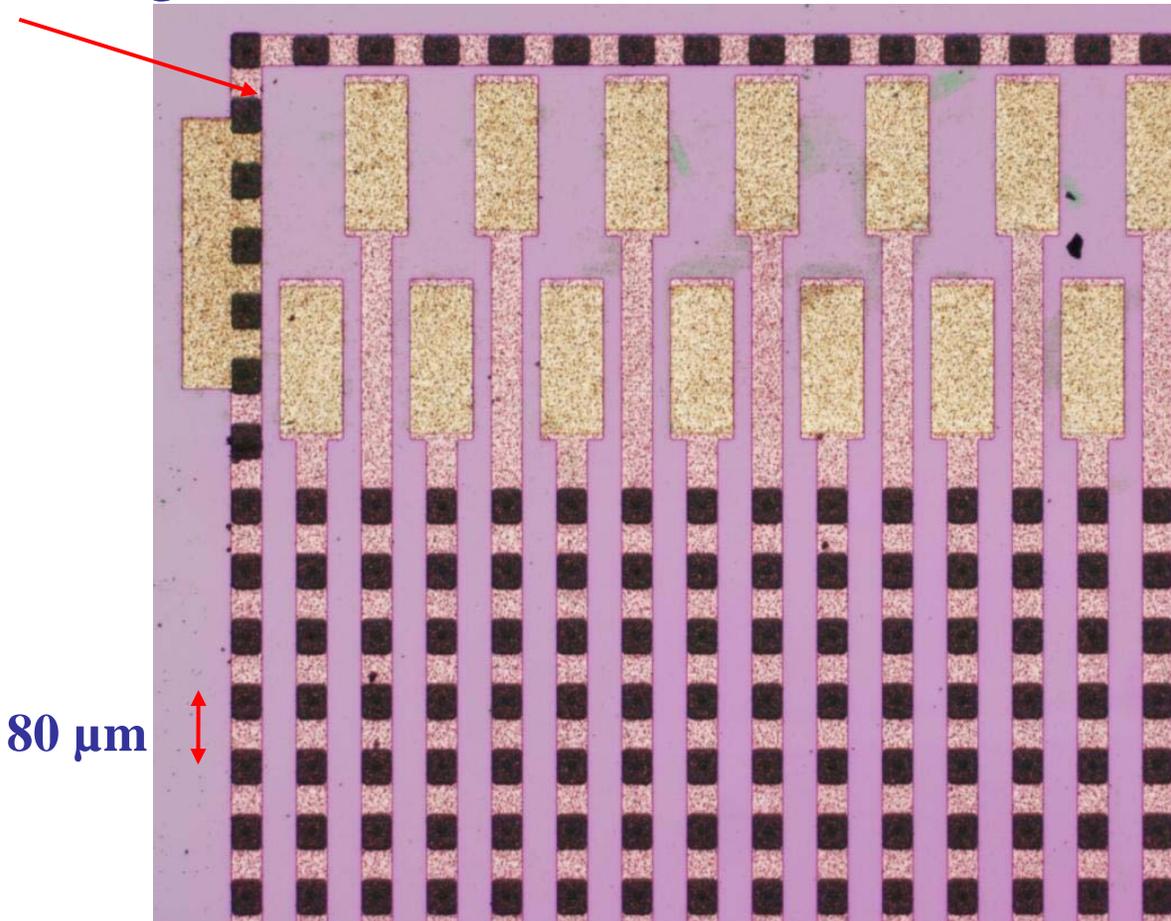


**Hole aspect ratio up to 25:1
(columns are 10 μm diameter,
250 μm deep)**



Strip detectors

3D guard ring



50 strips
DC coupled
50 electrodes/strip

80 μm

80 μm

Strip detectors

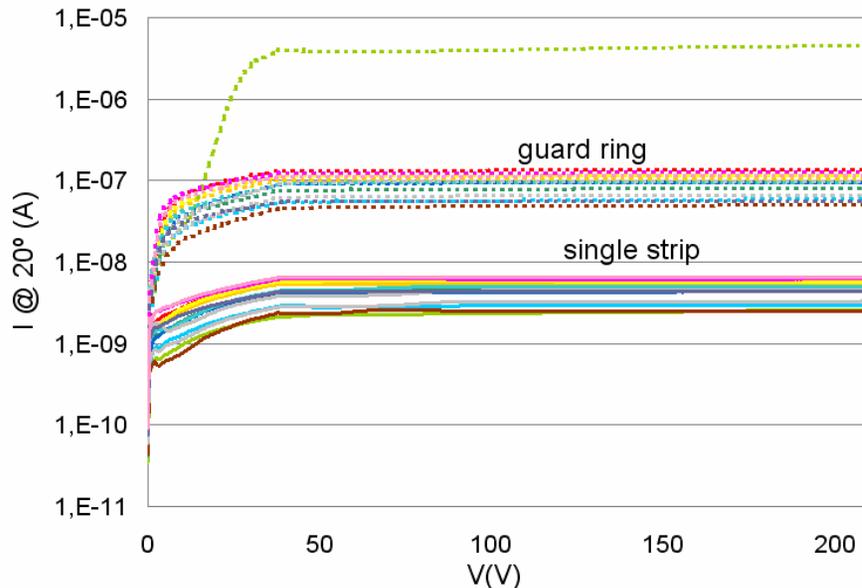
P-type

- VFD ~ 30V
- **2 – 6 nA/strip**, very homogeneous between wafers
- Only 2 detectors (of 16 tested) with breakdown < 50V -> **87.5%**

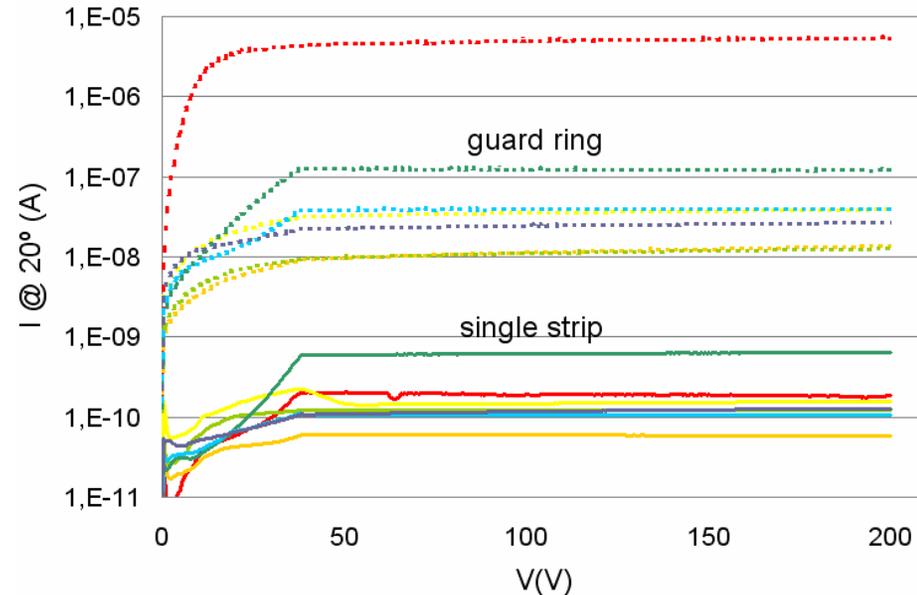
N-type

- VFD ~ 10V
- **0.1 – 0.6 nA/strip**
- Currents less homogeneous and stable than in the ptype
 - Beneficial effect of p-stops in the ptype sensors or effect of different doping profiles?
- 3 detectors (of 10) with BD < 50V -> **70%**

P-Type 3D strip detectors



N-Type 3D strip detectors



Strip detectors – Status and test plans

- A batch of double-sided 3D strip detectors has been irradiated at Karlsruhe with **26 MeV protons**.
 - Irradiations coordinated by Freiburg - thanks!
- Detectors will be distributed and tested with Alibava systems in **Glasgow, Freiburg, CNM**.
 - Aim for standardisation of measurements

Fluence (n_{eq}/cm^2)	# P devices	# N devices
5E14	2	0
1E15	2	0
2E15	2	2
5E15	2	0 (+2*)
1E16	2	2
2E16	2	2

(* first run)

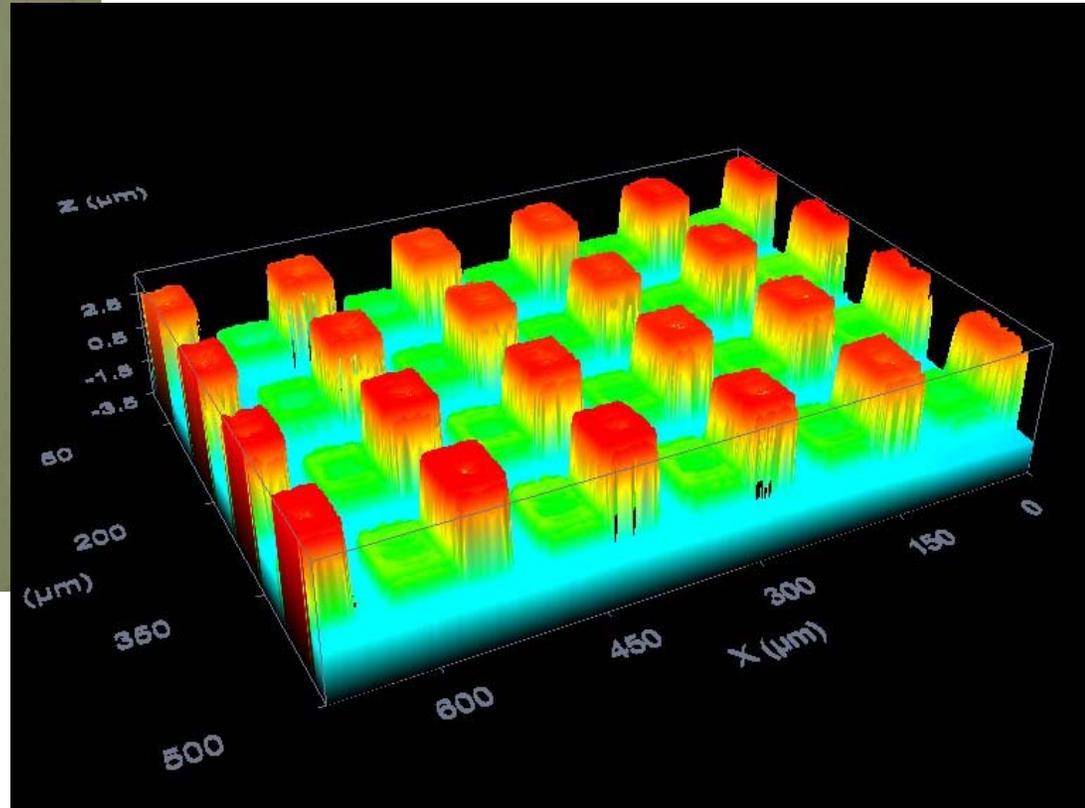
Al

N-hole (collecting electrode)

Polysilicon

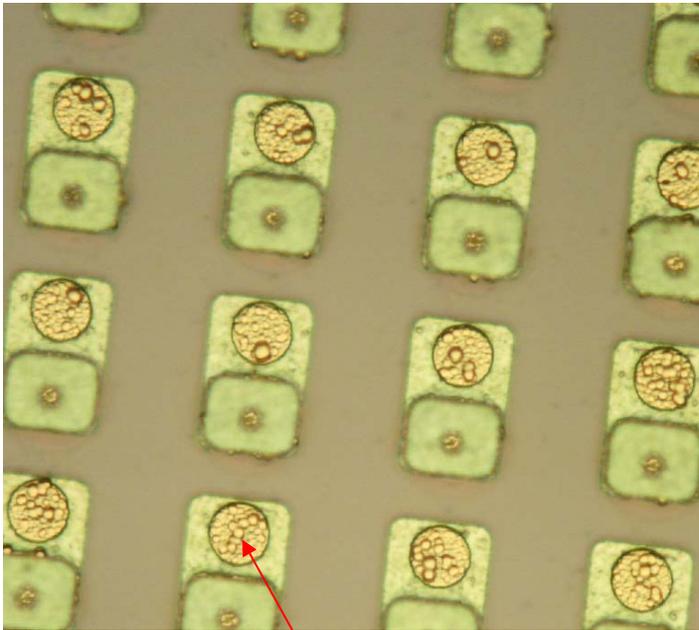
Individual pstop around each column

3D guard ring

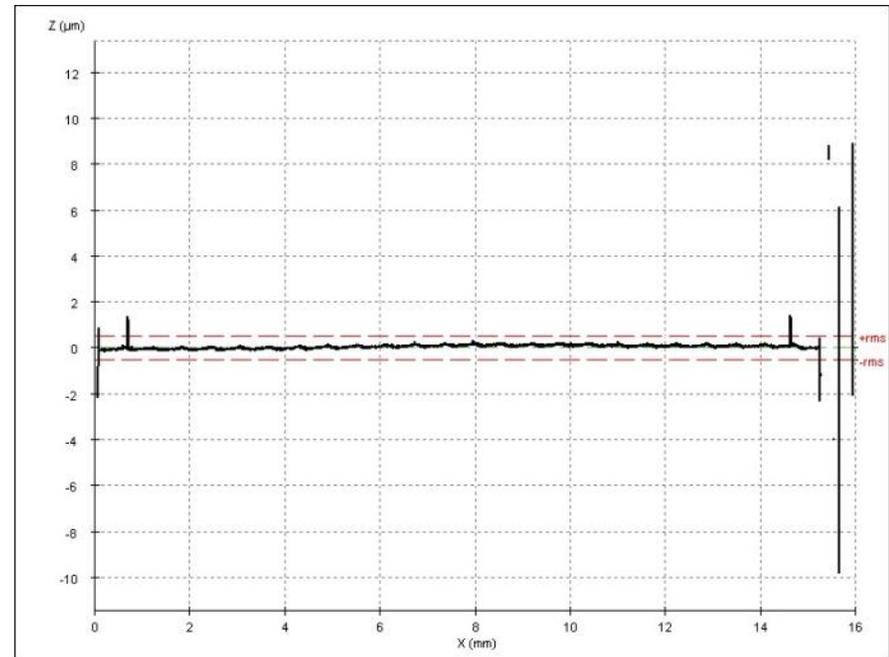


Medipix2 - Bump bonding and tests

- 18 sensors (10p+8n) were bump-bonded at **VTT** with Sn/Ag to **Medipix2** and **Timepix** chips (partially financed by RD50)
- Tested with microfocussed X-rays at the **Diamond Light Source Synchrotron** in May – see Chris's talk today

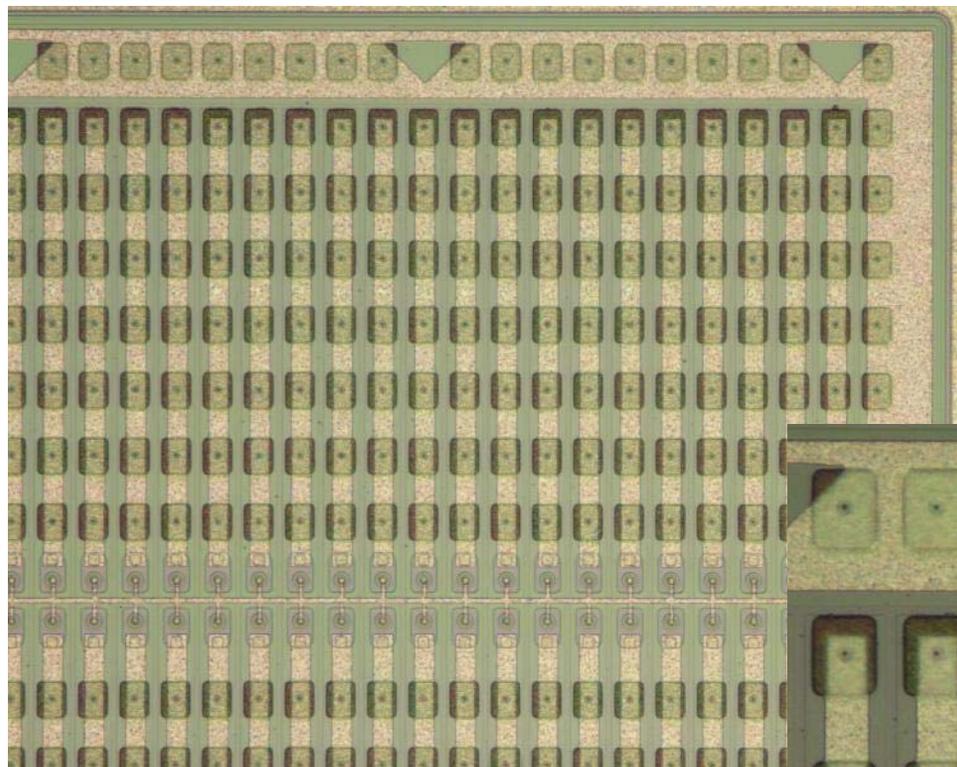


Electroless
Ni/Au UBM

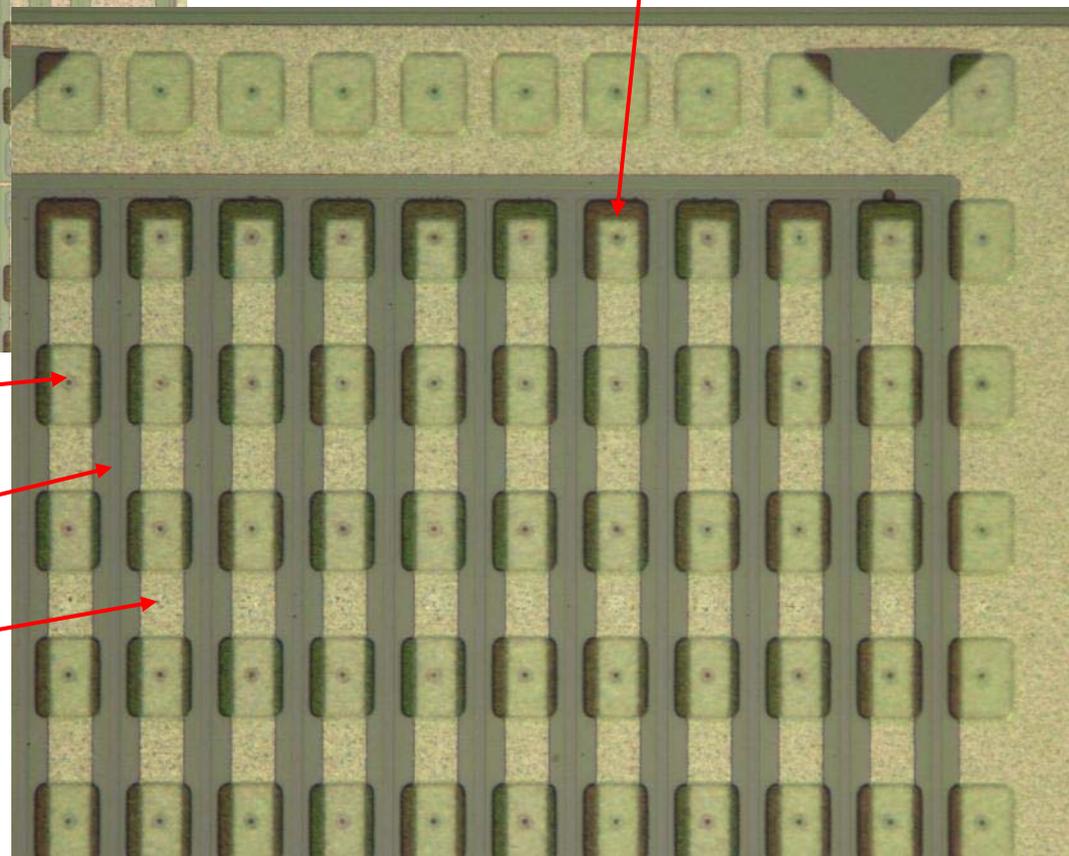


Curvature measured in Medipix2 chip

ATLAS pixels



Polysilicon

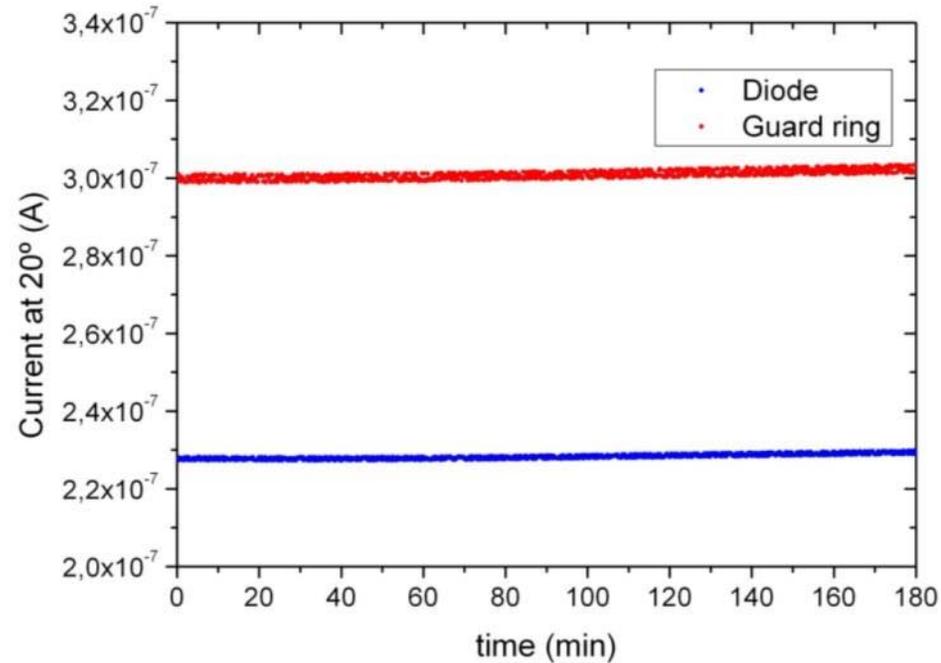
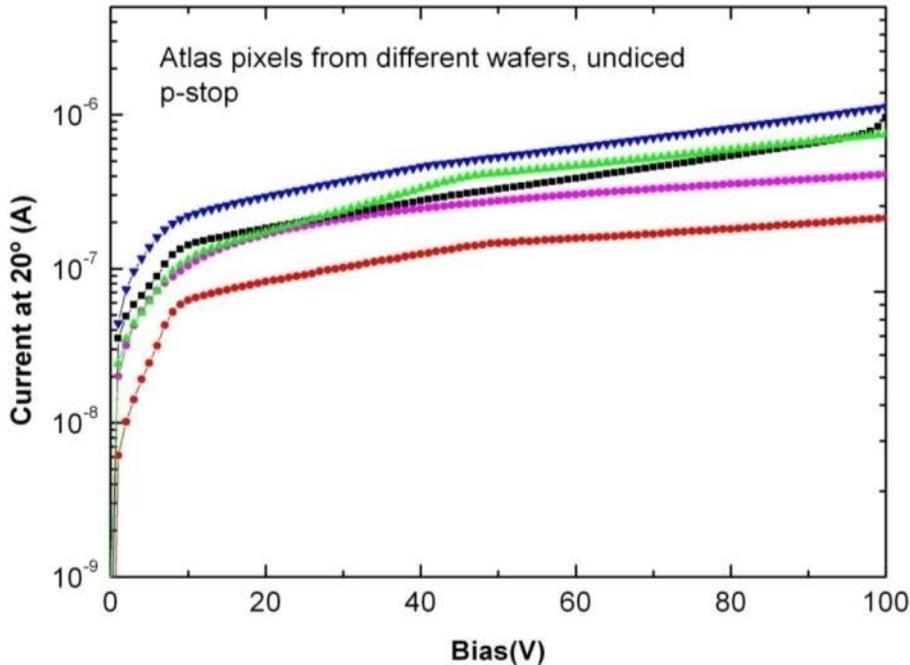


N-hole (p-holes in back, not visible)

P-stop

Al

ATLAS pixels



- **Current/pixel in full depletion, 20°C: 80-150 pA**
- **43% sensors with VBD > 50 V, I @ 50V, 20°C < 1uA**

- **Total current in p-type ATLAS sensor, 40V, 18°C**
- **2% variation in 3 hours**

ATLAS pixels - plans

Bump bonding

- 6 3D-ATLAS sensors sent to **VTT** to bump-bond to **FPIX** chip (partially financed by RD50)
- Glasgow in contact with **IZM** for bonding with **FE-I3**

Tests

- ATLAS pixels will be tested by Glasgow (FP420 ATLAS upgrade programme)
- IFAE (Institute for High Energy Physics, Barcelona) has acquired a TurboDAQ system – next year we'll be able to test ATLAS pixels in Barcelona
- Liverpool and CNM to produce fan-ins to test ATLAS pixels with strip readout – this will allow to test irradiated pixel detectors

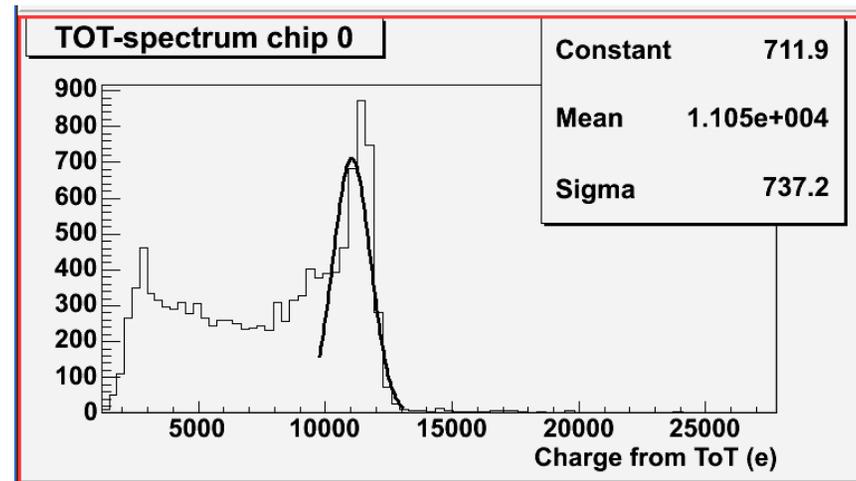
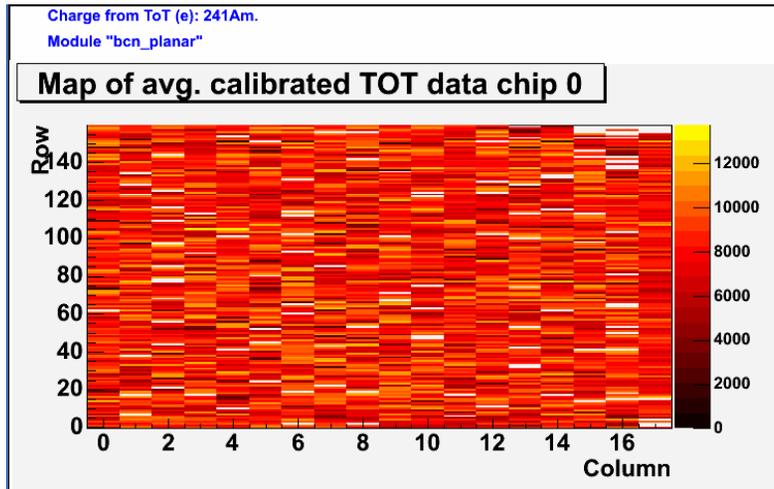
Bump bonding at CNM-IFAE

- Joint development CNM-IFAE (Institute of High Energy Physics, Barcelona)
- Class 100 clean room at CNM dedicated to packaging
- Techniques:
 - Manual SMD
 - Manual wirebonding
 - Flipchip
 - Standard temperatures
 - High temperatures: 280°C
- Equipment:
 - Dek248 screen printer
 - ATV reflow oven with vacuum
 - Manual Pick&Place machine
 - **SET FC150 flip chip machine**



Enric Cabruja (CNM) and Mokhtar Chemeissani (IFAE)

- SET/Süss Microtech FC150 for fine pitch flip chip
 - Installed early 2009
 - Efficiency in bump-bond contact > 99.5% (aim for 99.99% or better)
 - **First working ATLAS pixel sensor (planar) bonded in Spain two weeks ago!**
 - Aim to produce Medipix assemblies soon



First results using 241Am alpha source.
 Readout ATLAS FEI3 chip, tested at CERN, 22-May

3D fabrication:

- 14 wafers (8p + 6n) of double-sided 3D detectors fabricated at the CNM clean room
- **Double side processing has proved to be very reliable and repeatable**
- **Good tested sensors: 70% (N-strips), 87% (P-strips), 43% (P-ATLAS pixels)**
- **All fabrication steps available in-house**
- **CNM is able to do “large” productions**

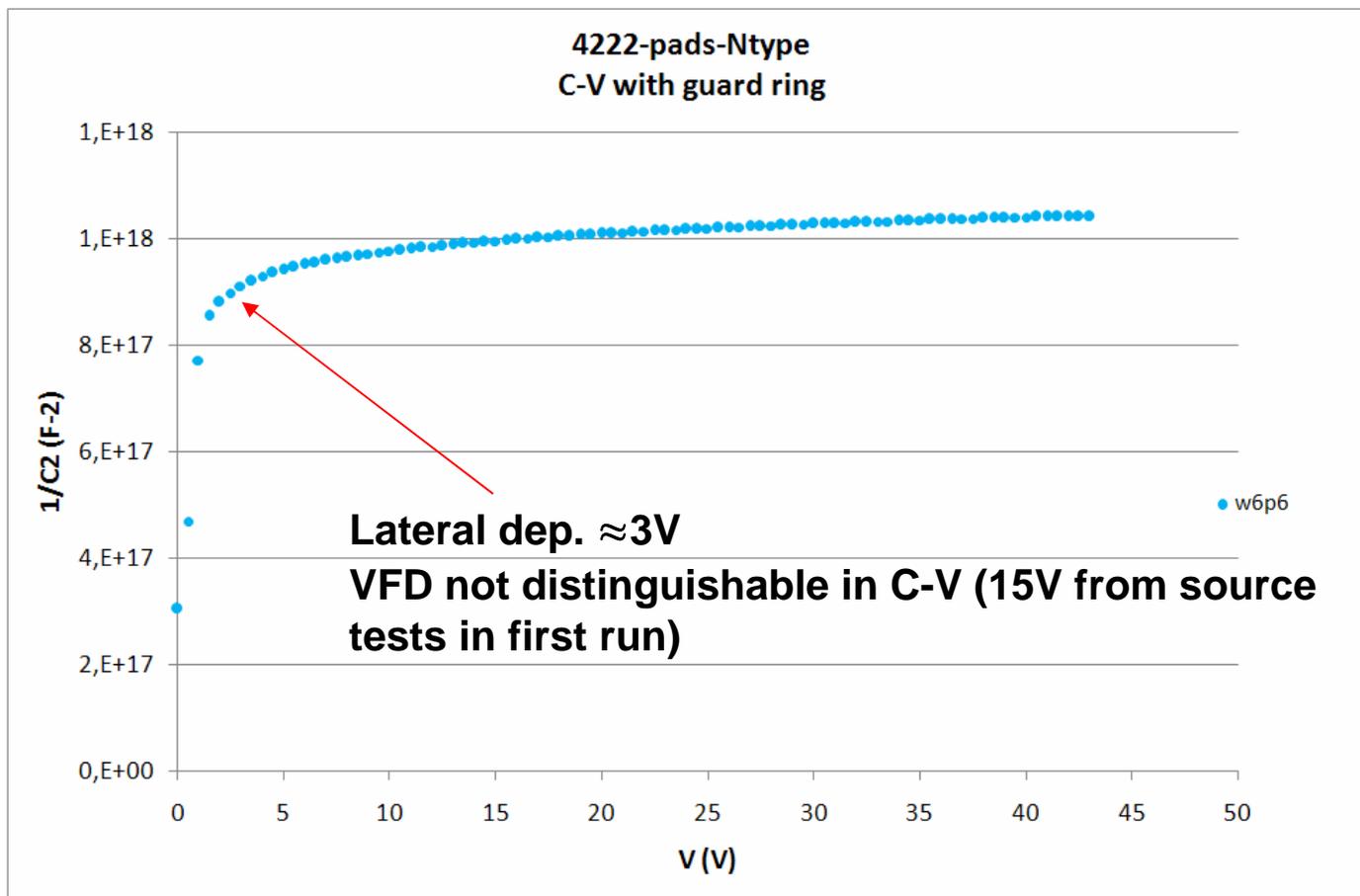
3D sensors:

- **Strip detectors irradiated up to $2 \times 10^{16} \text{ n}_{\text{eq}}/\text{cm}^2$**
- **Will be distributed for tests with ALIBAVA**
- **Medipix detectors successfully tested at the Diamond Light Source Synchrotron**

Bump bonding

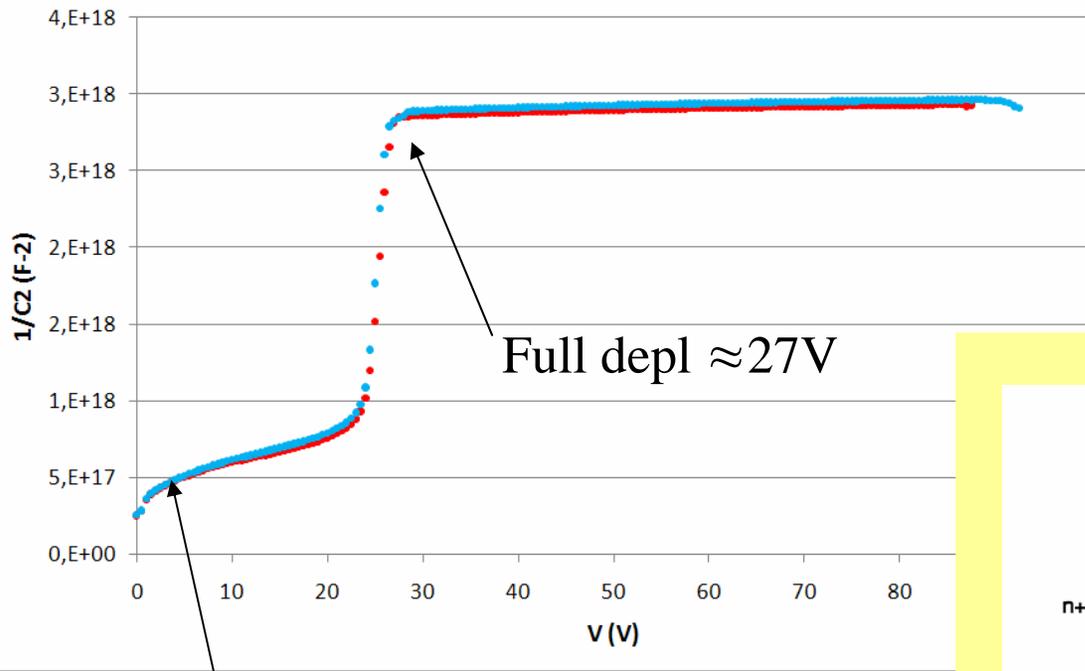
- **Fine pitch bump bonding achieved at IFAE-CNM**
 - **Contact efficiency > 99.5%**
 - **First working ATLAS pixel detector bump bonded**

Depletion n-type



Depletion p-type

P-type pad detector, pitch 55 μm



3V lateral depletion

